Heating Process

1 Total Mass Balance:

$$\frac{du}{dt} = \dot{m}_{in} - \dot{m}_{out}; \quad M = P.V$$

$$\frac{d(PV)}{dt} = \frac{P dV}{dt} = PF_{in} - PF_{out}$$

$$\frac{dv}{dt} = F_{in} - F_{out} ; Volume is controlled}$$

$$\Rightarrow V is constant$$

Fin: In Put flow rate

Fout: Output flow rate

Tin: In Put Temprature

Tout: Output Temprature

Cp: Heat Capacity Factor, const

Q: Mani Pulated Heat Rate

The system is isolated

No heat losses

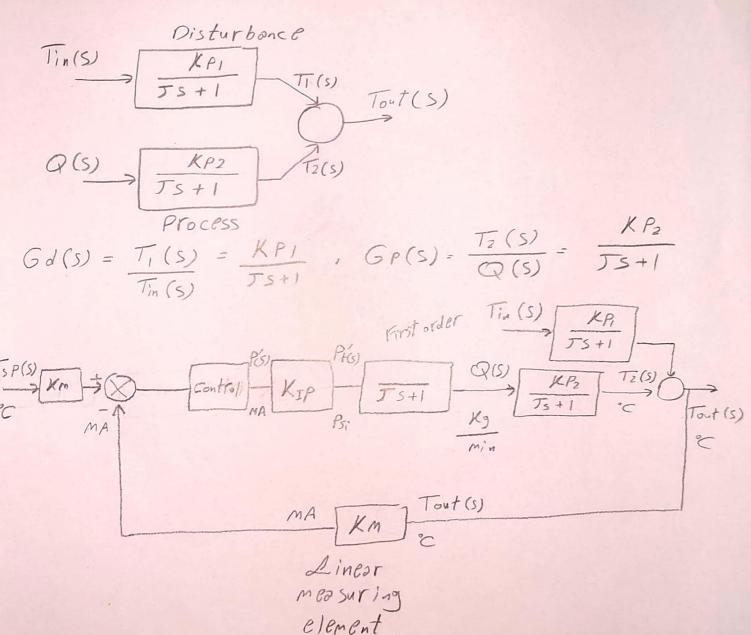
Time Constant

$$T = \frac{V}{F_{in}}, XP_{i} = 1$$

$$XP_{2} = \frac{1}{F_{in}PCP}$$

Q manipulated variable T controlled variable

Super Position



Enthalphy H= MCPT



Radiation

if we ignore Rediction

Jp dt +T = Toot Kpd Q

KP. - wiele ssaradio

Laplace, instal condition 'zero'

first order diffirential

equation

H. Entholphy M. mass of transistor

CP. Heat Capacity factor

T. Temprature of transistor

To aimbient temprature

E. Emissivity

d. Stefan Boltzman constant

A. Surface orea

M. overall heat transfare

Coeficient

Q. Heat output

Q. factor of the heater

(0-100%)

$$M = 0.00 | Kg$$
 $CP = 4900 \frac{J}{Kg \cdot K}$
 $U = 200 \frac{W}{M^2 K}$
 $A = \frac{2}{100^2} M^2$

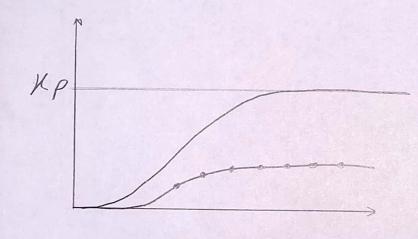
$$\int_{P} = (0,001 \, \text{Kg}) (4900 \, \frac{J}{\text{Kg} \cdot \text{K}}) \\
(200 \, \frac{W}{M^{2} \, \text{K}}) (0,0002 \, \text{M}^{2})$$

$$\int_{P} = 122.5 \, \frac{J}{W}$$

$$\int_{P} = 122.5 \, \text{S} ; [W] = [\frac{J}{S}]$$

$$T(s) = \frac{KP e^{-\theta Ps}}{TPS + 1}$$

Op Process dead time



The method approximate high order models to first order model+ dead time.

Tes Ponse and the interPolated answer.